

General Description

The MY8B06C uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

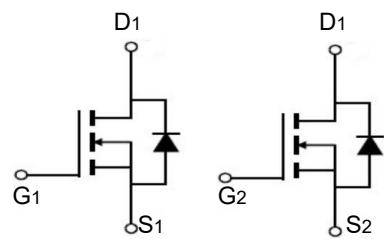
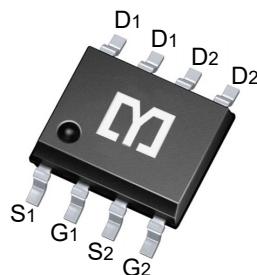


Features

| | | |
|---|----|------------------|
| V_{DSS} | 60 | V |
| I_D | 8 | A |
| $R_{DS(ON)}(\text{at } V_{GS}=10\text{V})$ | 28 | $\text{m}\Omega$ |
| $R_{DS(ON)}(\text{at } V_{GS}=4.5\text{V})$ | 36 | $\text{m}\Omega$ |

Application

- Battery protection
- Load switch
- Uninterruptible power supply



Package Marking and Ordering Information

| Product ID | Pack | Marking | Qty(PCS) |
|------------|-------|---------|----------|
| MY8B06C | SOP-8 | MY8B06C | 3000 |

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Rating | Units |
|------------------------------|---|------------|-------|
| V_{DS} | Drain-Source Voltage | 60 | V |
| V_{GS} | Gate-Source Voltage | ± 20 | V |
| $I_D @ T_A=25^\circ\text{C}$ | Continuous Drain Current, $V_{GS} @ 10\text{V}^1$ | 8.0 | A |
| $I_D @ T_A=70^\circ\text{C}$ | Continuous Drain Current, $V_{GS} @ 10\text{V}^1$ | 4.5 | A |
| I_{DM} | Pulsed Drain Current ² | 22 | A |
| EAS | Single Pulse Avalanche Energy ³ | 22 | mJ |
| I_{AS} | Avalanche Current | 23 | A |
| $P_D @ T_A=25^\circ\text{C}$ | Total Power Dissipation ⁴ | 1.5 | W |
| T_{STG} | Storage Temperature Range | -55 to 150 | C |
| T_J | Operating Junction Temperature Range | -55 to 150 | C |

Thermal Data

| Symbol | Parameter | Typ. | Max. | Unit |
|-----------------|--|------|------|------|
| $R_{\theta JA}$ | Thermal Resistance Junction-ambient ¹ | --- | 85 | C/ W |
| $R_{\theta JC}$ | Thermal Resistance Junction-Case ¹ | --- | 25 | C/ W |

Electrical Characteristics ($T_j=25^\circ\text{C}$, unless otherwise noted)

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Units |
|--|--|--|------|------|-----------|------------------|
| Off Characteristic | | | | | | |
| $V_{(\text{BR})\text{DSS}}$ | Drain- Source Breakdown Voltage | $V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$ | 60 | - | - | V |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS}=60\text{V}$, $V_{GS} = 0\text{V}$, | - | - | 1.0 | μA |
| I_{GSS} | Gate to Body Leakage Current | $V_{DS}=0\text{V}$, $V_{GS} = \pm 20\text{V}$ | - | - | ± 100 | nA |
| On Characteristics | | | | | | |
| $V_{GS(\text{th})}$ | Gate Threshold Voltage | $V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$ | 1.0 | 1.6 | 2.5 | V |
| $R_{DS(\text{on})}$ | Static Drain- Source on- Resistance note3 | $V_{GS}=10\text{V}$, $I_D=5\text{A}$ | - | 28 | 40 | $\text{m}\Omega$ |
| | | $V_{GS}=4.5\text{V}$, $I_D=3\text{A}$ | - | 36 | 50 | |
| Dynamic Characteristics | | | | | | |
| C_{iss} | Input Capacitance | $V_{DS}=25\text{V}$, $V_{GS}=0\text{V}$, $f=1.0\text{MHz}$ | - | 1148 | - | pF |
| C_{oss} | Output Capacitance | | - | 58.5 | - | pF |
| C_{rss} | Reverse Transfer Capacitance | | - | 49.4 | - | pF |
| Q_g | Total Gate Charge | | - | 20.3 | - | nC |
| Q_{gs} | Gate- Source Charge | $V_{DS}=30\text{V}$, $I_D=2.5\text{A}$, $V_{GS}=10\text{V}$ | - | 3.7 | - | nC |
| Q_{gd} | Gate-Drain("Miller") Charge | | - | 5.3 | - | nC |
| Switching Characteristics | | | | | | |
| $t_{d(on)}$ | Turn- on Delay Time | $V_{DS}=30\text{V}$, $I_D=5\text{A}$, $R_G=1.8\Omega$, $V_{GS}=10\text{V}$ | - | 7.6 | - | ns |
| t_r | Turn- on Rise Time | | - | 20 | - | ns |
| $t_{d(off)}$ | Turn- off Delay Time | | - | 15 | - | ns |
| t_f | Turn- off Fall Time | | - | 24 | - | ns |
| Drain- Source Diode Characteristics and Maximum Ratings | | | | | | |
| I_s | Maximum Continuous Drain to Source Diod Forward | $V_{GS}=0\text{V}$, $I_s=5\text{A}$ | - | - | 5 | A |
| I_{SM} | Maximum Pulsed Drain to Source Diode Forward Current | | - | - | 20 | A |
| V_{SD} | Drain to Source Diode Forward | $V_{GS}=0\text{V}$, $I_s=5\text{A}$ | - | - | 1.2 | V |
| trr | Body Diode Reverse Recovery Time | $I_F=5\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$ | - | 29 | - | ns |
| Qrr | Body Diode Reverse Recove | | - | 43 | - | nC |

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : $T_j=25^\circ\text{C}$, $V_{DD}=30\text{V}$, $V_G=10\text{V}$, $L=0.5\text{mH}$, $R_G=25\Omega$, $I_{AS}=8.7\text{A}$ 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$

Typical Characteristics

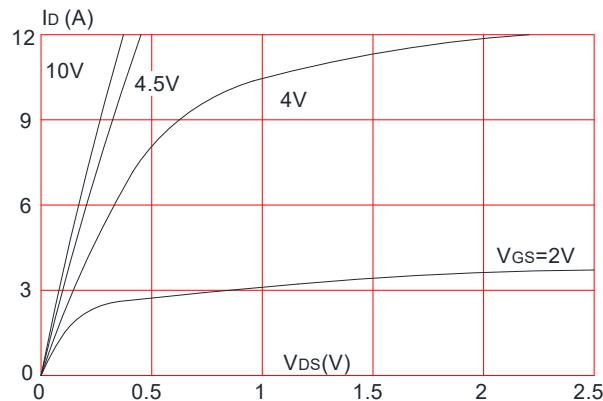
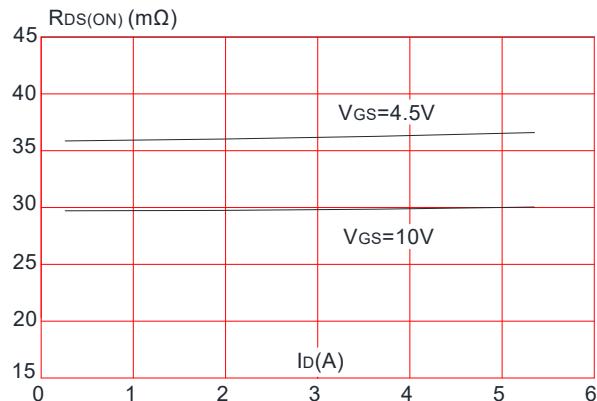
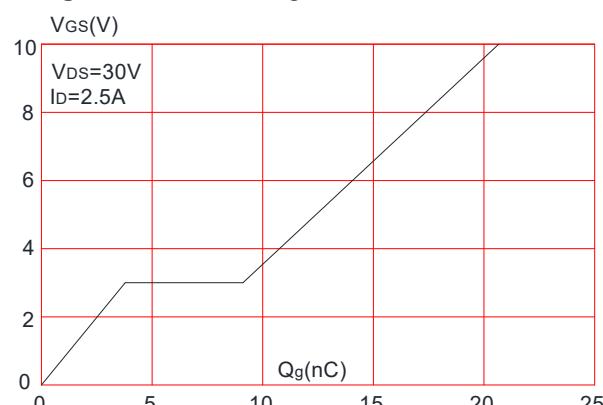
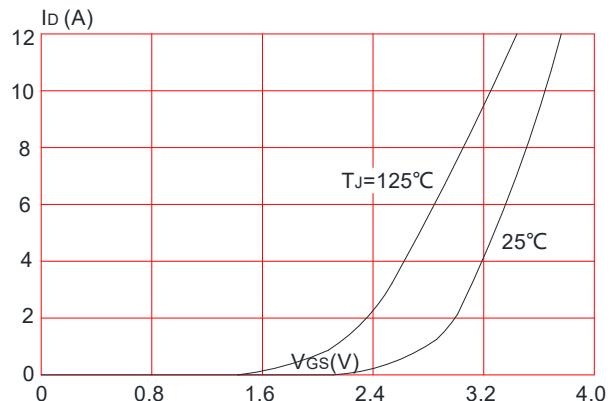
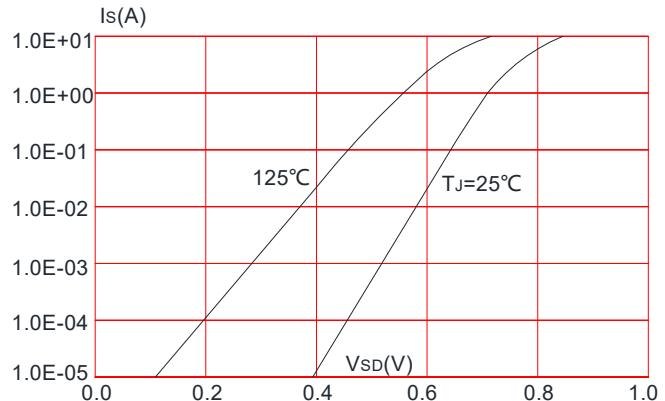
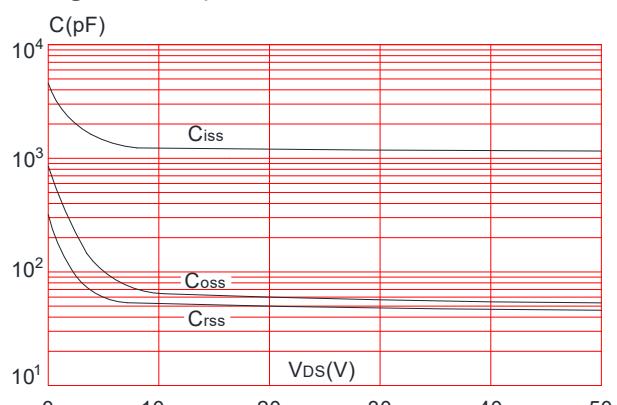
Figure1: Output Characteristics**Figure 3:** On-resistance vs. Drain Current**Figure 5:** Gate Charge Characteristics**Figure 2:** Typical Transfer Characteristics**Figure 4:** Body Diode Characteristics**Figure 6:** Capacitance Characteristics

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

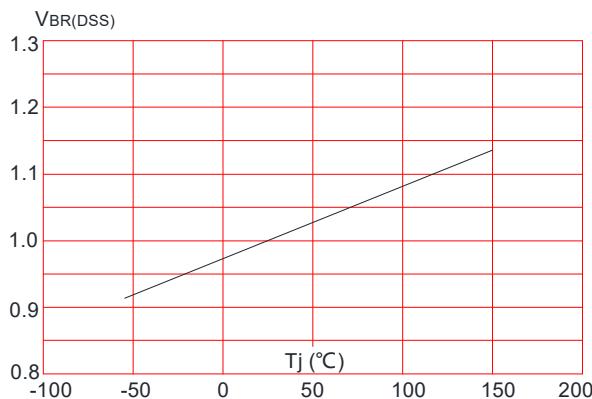


Figure 8: Normalized on Resistance vs. Junction Temperature

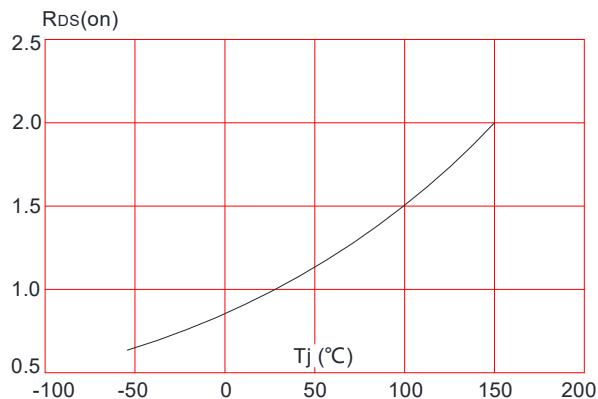


Figure 9: Maximum Safe Operating Area

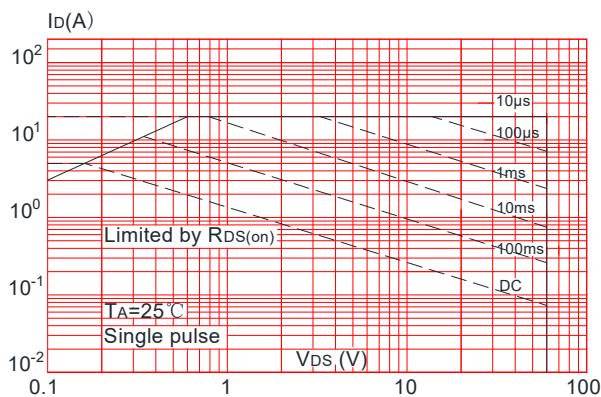


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

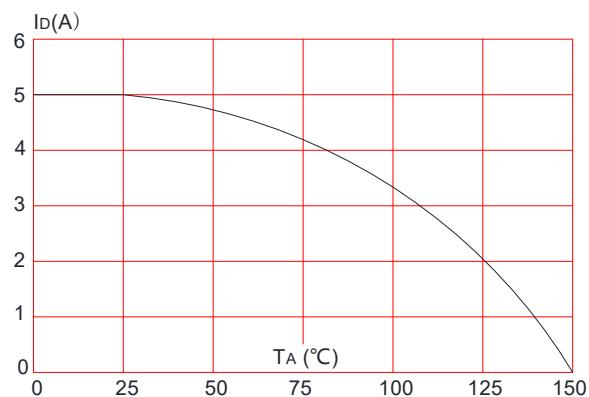
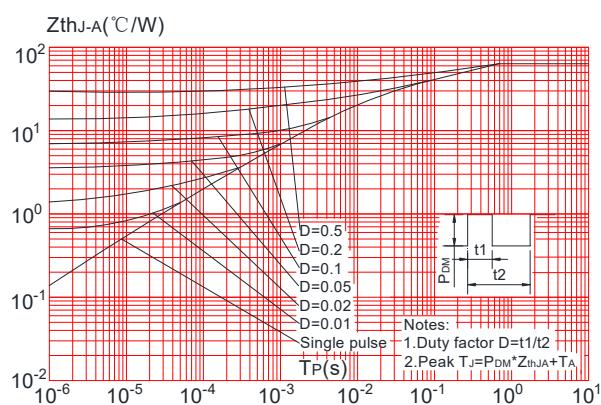
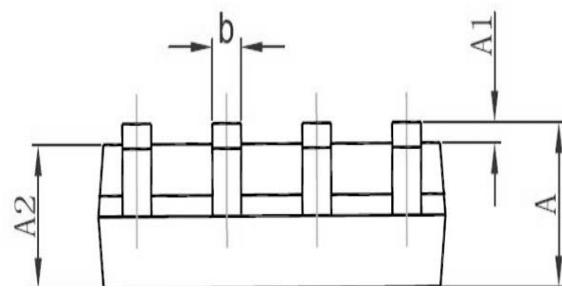
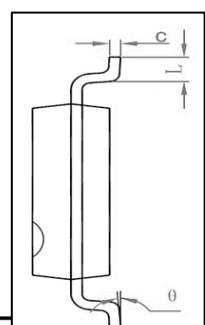
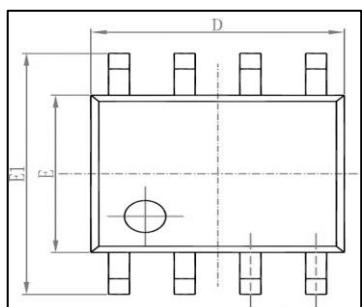


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Package Mechanical Data-SOP-8



| Symbol | Dimensions in Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 1.350 | 1.750 | 0.053 | 0.069 |
| A1 | 0.100 | 0.250 | 0.004 | 0.010 |
| A2 | 1.350 | 1.550 | 0.053 | 0.061 |
| b | 0.330 | 0.510 | 0.013 | 0.020 |
| c | 0.170 | 0.250 | 0.006 | 0.010 |
| D | 4.700 | 5.100 | 0.185 | 0.200 |
| E | 3.800 | 4.000 | 0.150 | 0.157 |
| E1 | 5.800 | 6.200 | 0.228 | 0.244 |
| e | 1.270 (BSC) | | 0.050 (BSC) | |
| L | 0.400 | 1.270 | 0.016 | 0.050 |
| θ | 0° | 8° | 0° | 8° |

